

BLC9H10XS-606A

Power LDMOS transistor

Rev. 1 — 24 March 2020

AMPLEON

Product data sheet

1. Product profile

1.1 General description

600 W LDMOS packaged asymmetric Doherty power transistor for base station applications at frequencies from 616 MHz to 960 MHz.

Table 1. Typical performance 634.5/737 MHz

Typical RF performance at $T_{case} = 25\text{ °C}$ in an asymmetrical Doherty demo circuit. $V_{DS} = 50\text{ V}$; $I_{Dq} = 400\text{ mA}$ (main); $V_{GS(amp)peak} = 0.7\text{ V}$, unless otherwise specified.

| Test signal | f | V_{DS} | $P_{L(AV)}$ | G_p | η_D | ACPR |
|------------------|------------|----------|-------------|-------|----------|--------------|
| | (MHz) | (V) | (dBm) | (dB) | (%) | (dBc) |
| 1-carrier W-CDMA | 617 to 652 | 50 | 49.2 | 19.1 | 52.3 | -33.5 [1][2] |
| | 728 to 746 | 50 | 49.2 | 19.5 | 50.2 | -35 [1][2] |

[1] Test signal: 1-carrier W-CDMA; 3GPP test model 1; 64 DPCH; PAR = 9.6 dB at 0.01 % probability on CCDF.

[2] Test data is based on wideband demo measurement (f = 617 MHz to 746 MHz).

Table 2. Typical performance 789.5 MHz

Typical RF performance at $T_{case} = 25\text{ °C}$ in an asymmetrical Doherty demo circuit. $V_{DS} = 48\text{ V}$; $I_{Dq} = 500\text{ mA}$ (main); $V_{GS(amp)peak} = 0.05\text{ V}$, unless otherwise specified.

| Test signal | f | V_{DS} | $P_{L(AV)}$ | G_p | η_D | ACPR |
|------------------|------------|----------|-------------|-------|----------|-----------|
| | (MHz) | (V) | (dBm) | (dB) | (%) | (dBc) |
| 1-carrier W-CDMA | 758 to 821 | 48 | 50.5 | 18.8 | 55.5 | -29.3 [1] |

[1] Test signal: 1-carrier W-CDMA; 3GPP test model 1; 64 DPCH; PAR = 9.6 dB at 0.01 % probability on CCDF.

Table 3. Typical performance 881.5 MHz

Typical RF performance at $T_{case} = 25\text{ °C}$ in an asymmetrical Doherty demo circuit. $V_{DS} = 48\text{ V}$; $I_{Dq} = 400\text{ mA}$ (main); $V_{GS(amp)peak} = 0.05\text{ V}$, unless otherwise specified.

| Test signal | f | V_{DS} | $P_{L(AV)}$ | G_p | η_D | ACPR |
|------------------|------------|----------|-------------|-------|----------|-----------|
| | (MHz) | (V) | (dBm) | (dB) | (%) | (dBc) |
| 1-carrier W-CDMA | 869 to 894 | 48 | 50.5 | 17.9 | 53.2 | -30.2 [1] |

[1] Test signal: 1-carrier W-CDMA; 3GPP test model 1; 64 DPCH; PAR = 9.6 dB at 0.01 % probability on CCDF.

Table 4. Typical performance 942 MHz

Typical RF performance at $T_{case} = 25\text{ °C}$ in an asymmetrical Doherty demo circuit. $V_{DS} = 48\text{ V}$; $I_{Dq} = 350\text{ mA}$ (main); $V_{GS(amp)peak} = 0.05\text{ V}$, unless otherwise specified.

| Test signal | f | V_{DS} | $P_{L(AV)}$ | G_p | η_D | ACPR |
|------------------|------------|----------|-------------|-------|----------|-----------|
| | (MHz) | (V) | (dBm) | (dB) | (%) | (dBc) |
| 1-carrier W-CDMA | 925 to 960 | 48 | 50.5 | 17.2 | 54.7 | -29.2 [1] |

[1] Test signal: 1-carrier W-CDMA; 3GPP test model 1; 64 DPCH; PAR = 9.6 dB at 0.01 % probability on CCDF.

1.2 Features and benefits

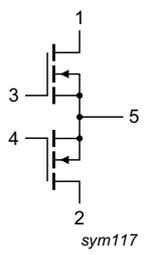
- Excellent ruggedness
- High efficiency
- Low thermal resistance providing excellent thermal stability
- Lower output capacitance for improved performance in Doherty applications
- Designed for low memory effects providing excellent digital pre-distortion capability
- Internally matched for ease of use
- Integrated ESD protection
- For RoHS compliance see the product details on the Ampleon website

1.3 Applications

- RF power amplifiers for base stations and multi carrier applications in the 616 MHz to 960 MHz frequency range

2. Pinning information

Table 5. Pinning

| Pin | Description | Simplified outline | Graphic symbol |
|-----|----------------------------|---|--|
| 1 | drain1 |  |  |
| 2 | drain2 | | |
| 3 | gate1 | | |
| 4 | gate2 | | |
| 5 | source [1] | | |

[1] Connected to flange.

3. Ordering information

Table 6. Ordering information

| Type number | Package | | |
|----------------|---------|---|-----------|
| | Name | Description | Version |
| BLC9H10XS-606A | - | plastic earless flanged cavity package; 4 leads | SOT1250-4 |

4. Limiting values

Table 7. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|-------------------|------------------------------------|------------|-----|-----|------|
| V_{DS} | drain-source voltage | | - | 110 | V |
| $V_{GS(amp)main}$ | main amplifier gate-source voltage | | -6 | +11 | V |
| $V_{GS(amp)peak}$ | peak amplifier gate-source voltage | | -6 | +11 | V |

Table 7. Limiting values ...continued
 In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|-------------------|----------------------|------------|-----|------|------|
| T _{stg} | storage temperature | | -65 | +150 | °C |
| T _j | junction temperature | [1] | - | 225 | °C |
| T _{case} | case temperature | [1] | -40 | +150 | °C |

[1] Continuous use at maximum temperature will affect the reliability, for details refer to the online MTF calculator.

5. Thermal characteristics

Table 8. Thermal characteristics

| Symbol | Parameter | Conditions | Typ | Unit |
|----------------------|--|---|-------|------|
| R _{th(j-c)} | thermal resistance from junction to case | V _{DS} = 50 V; I _{Dq} = 600 mA (main); V _{GS(amp)peak} = 0.5 V; T _{case} = 80 °C | | |
| | | P _L = 112 W | 0.236 | K/W |
| | | P _L = 141 W | 0.198 | K/W |

6. Characteristics

Table 9. DC characteristics
 T_j = 25 °C unless otherwise specified.

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|----------------------|----------------------------------|--|-----|------|-----|------|
| Main device | | | | | | |
| V _{(BR)DSS} | drain-source breakdown voltage | V _{GS} = 0 V; I _D = 1.5 mA | 110 | - | - | V |
| V _{GS(th)} | gate-source threshold voltage | V _{DS} = 10 V; I _D = 150 mA | 1.5 | 2.0 | 2.5 | V |
| V _{GSq} | gate-source quiescent voltage | V _{DS} = 47 V; I _D = 600 mA | - | 2 | - | V |
| I _{DSS} | drain leakage current | V _{GS} = 0 V; V _{DS} = 50 V | - | - | 1.4 | µA |
| I _{DSX} | drain cut-off current | V _{GS} = V _{GS(th)} + 3.75 V; V _{DS} = 10 V | - | 24.5 | - | A |
| I _{GSS} | gate leakage current | V _{GS} = 11 V; V _{DS} = 0 V | - | - | 140 | nA |
| g _{fs} | forward transconductance | V _{DS} = 10 V; I _D = 7.5 A | - | 9.8 | - | S |
| R _{DS(on)} | drain-source on-state resistance | V _{GS} = V _{GS(th)} + 3.75 V; I _D = 5.25 A | - | 160 | 203 | mΩ |
| Peak device | | | | | | |
| V _{(BR)DSS} | drain-source breakdown voltage | V _{GS} = 0 V; I _D = 3 mA | 110 | - | - | V |
| V _{GS(th)} | gate-source threshold voltage | V _{DS} = 10 V; I _D = 300 mA | 1.5 | 2.0 | 2.5 | V |
| V _{GSq} | gate-source quiescent voltage | V _{DS} = 47 V; I _D = 1200 mA | - | 2 | - | V |
| I _{DSS} | drain leakage current | V _{GS} = 0 V; V _{DS} = 50 V | - | - | 2.8 | µA |
| I _{DSX} | drain cut-off current | V _{GS} = V _{GS(th)} + 3.75 V; V _{DS} = 10 V | - | 49.0 | - | A |
| I _{GSS} | gate leakage current | V _{GS} = 11 V; V _{DS} = 0 V | - | - | 280 | nA |
| g _{fs} | forward transconductance | V _{DS} = 10 V; I _D = 15.0 A | - | 18.7 | - | S |
| R _{DS(on)} | drain-source on-state resistance | V _{GS} = V _{GS(th)} + 3.75 V; I _D = 10.5 A | - | 82 | 107 | mΩ |

Table 10. RF characteristics

Test signal: 1-carrier W-CDMA; PAR = 7.2 dB at 0.01 % probability on the CCDF; 3GPP test model 1; 1 to 64 DPCH; $f_1 = 760.5$ MHz; $f_2 = 800.5$ MHz; RF performance at $V_{DS} = 48$ V; $I_{Dq} = 550$ mA (main); $V_{GS(amp)peak} = 0.5$ V; $T_{case} = 25$ °C; unless otherwise specified; in an asymmetrical Doherty production test circuit at frequencies from 758 MHz to 803 MHz.

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|-----------|------------------------------|---------------------|------|------|-----|------|
| G_p | power gain | $P_{L(AV)} = 107$ W | 16.8 | 18 | - | dB |
| RL_{in} | input return loss | $P_{L(AV)} = 107$ W | - | -13 | -8 | dB |
| η_D | drain efficiency | $P_{L(AV)} = 107$ W | 48 | 53.8 | - | % |
| ACPR | adjacent channel power ratio | $P_{L(AV)} = 107$ W | - | -31 | -26 | dBc |

Table 11. RF characteristics

Test signal: pulsed CW, $t_p = 100$ μ s; $\delta = 10$ %; $f = 803$ MHz; RF performance at $V_{DS} = 48$ V; $I_{Dq} = 550$ mA; $V_{GS(amp)peak} = 0.5$ V; $T_{case} = 25$ °C; unless otherwise specified; in a Doherty production test circuit.

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------|---------------------------------------|------------|-----|-----|-----|------|
| $P_{L(3dB)}$ | output power at 3 dB gain compression | - | 485 | 630 | - | W |

7. Test information

7.1 Ruggedness in Doherty operation

The BLC9H10XS-606A is capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: $V_{DS} = 48$ V; $I_{Dq} = 550$ mA; $V_{GS(amp)peak} = 0.5$ V; $f = 758$ MHz; $P_L = 200$ W (5 dB OBO); 1-carrier W-CDMA; PAR = 7.2 dB at 0.01 % probability on the CCDF; 3GPP test model 1; 1 to 64 DPCH.

7.2 Impedance information

Table 12. Typical impedance of main device

Measured load-pull data of main device; $I_{Dq} = 900$ mA (main); $V_{DS} = 48$ V; pulsed CW ($t_p = 100$ μ s; $\delta = 10$ %).

| f (MHz) | Z_S [1] (Ω) | Z_L [1] (Ω) | P_L [2] (W) | η_D [2] (%) | G_p [2] (dB) |
|--------------------------------------|---------------------------|---------------------------|------------------|---------------------|-------------------|
| Maximum power load | | | | | |
| 780 | 4.3 – j4.5 | 1.6 + j0.2 | 304 | 66.0 | 19.1 |
| 800 | 4.4 – j4.9 | 1.6 + j0.2 | 303 | 64.7 | 19.1 |
| 820 | 4.6 – j5.3 | 1.6 + j0.2 | 303 | 65.0 | 19.2 |
| 840 | 4.7 – j5.6 | 1.6 + j0.2 | 308 | 65.6 | 19.1 |
| Maximum drain efficiency load | | | | | |
| 780 | 4.3 – j4.5 | 2.0 + j1.0 | 244 | 70.7 | 20.8 |
| 800 | 4.4 – j4.9 | 1.4 + j1.0 | 233 | 70.1 | 20.7 |
| 820 | 4.6 – j5.3 | 1.4 + j1.2 | 209 | 72.2 | 21.2 |
| 840 | 4.7 – j5.6 | 1.4 + j1.2 | 206 | 72.5 | 21.2 |

[1] Z_S and Z_L defined in [Figure 1](#).

[2] At 3 dB gain compression.

Table 13. Typical impedance of peak device

Measured load-pull data of peak device; $I_{Dq} = 1800 \text{ mA (peak)}$; $V_{DS} = 48 \text{ V}$; pulsed CW ($t_p = 100 \mu\text{s}$; $\delta = 10 \%$).

| f | Z _S [1] | Z _L [1] | P _L [2] | η _D [2] | G _p [2] |
|--------------------------------------|--------------------|--------------------|--------------------|--------------------|--------------------|
| (MHz) | (Ω) | (Ω) | (W) | (%) | (dB) |
| Maximum power load | | | | | |
| 780 | 2.5 – j2.8 | 1.0 – j0.1 | 620 | 65.7 | 17.8 |
| 800 | 2.5 – j3.0 | 1.0 – j0.1 | 633 | 65.9 | 17.8 |
| 820 | 2.7 – j3.2 | 1.0 – j0.1 | 631 | 64.8 | 17.6 |
| 840 | 2.7 – j3.3 | 1.0 – j0.1 | 639 | 64.8 | 17.7 |
| Maximum drain efficiency load | | | | | |
| 780 | 2.5 – j2.8 | 0.6 + j0.6 | 371 | 75.6 | 20.5 |
| 800 | 2.5 – j3.0 | 0.6 + j0.6 | 375 | 78.8 | 20.8 |
| 820 | 2.7 – j3.2 | 0.6 + j0.4 | 447 | 77.9 | 19.5 |
| 840 | 2.7 – j3.3 | 0.6 + j0.4 | 447 | 77.2 | 19.8 |

[1] Z_S and Z_L defined in Figure 1.

[2] At 3 dB gain compression.

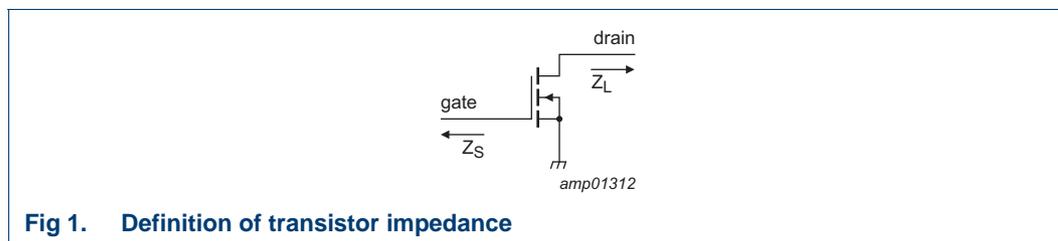


Fig 1. Definition of transistor impedance

7.3 Test circuit

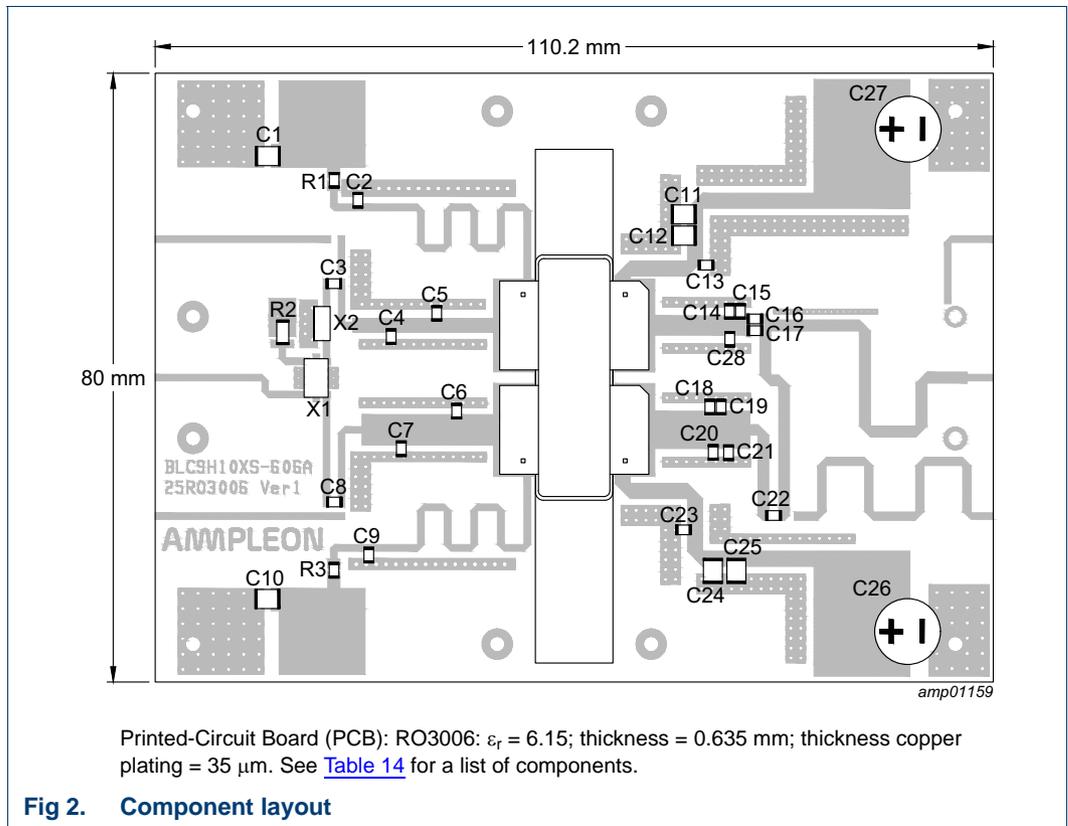


Fig 2. Component layout

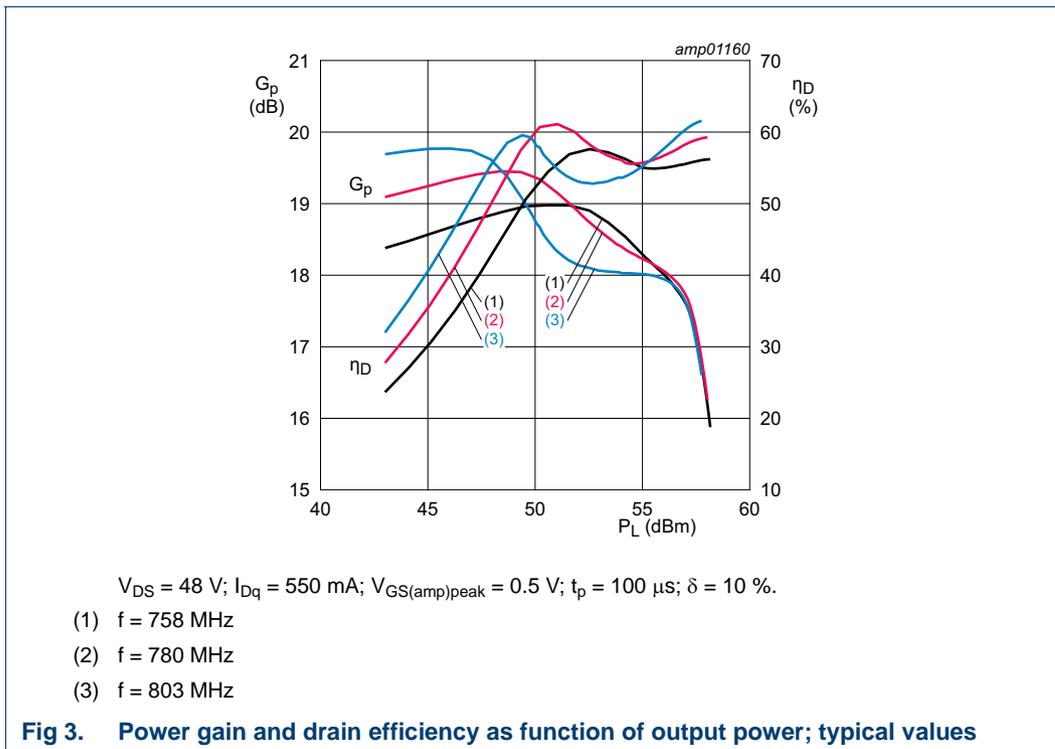
Table 14. List of components

See [Figure 2](#) for component layout.

| Component | Description | Value | Remarks |
|-------------------------------|-----------------------------------|----------------------------|-----------------------|
| C1, C10 | multilayer ceramic chip capacitor | 10 μF , 50 V | Murata: Hi-Q SMD 1210 |
| C2, C3, C8, C9, C13, C22, C23 | multilayer ceramic chip capacitor | 68 pF | Murata: Hi-Q SMD 0805 |
| C4 | multilayer ceramic chip capacitor | 3.9 pF | Murata: Hi-Q SMD 0805 |
| C5, C15 | multilayer ceramic chip capacitor | 4.7 pF | Murata: Hi-Q SMD 0805 |
| C6, C7 | multilayer ceramic chip capacitor | 5.6 pF | Murata: Hi-Q SMD 0805 |
| C11, C12, C24, C25 | multilayer ceramic chip capacitor | 10 μF , 100 V | Murata: Hi-Q SMD 1210 |
| C14 | multilayer ceramic chip capacitor | 4.3 pF | Murata: Hi-Q SMD 0805 |
| C16, C17, C18 | multilayer ceramic chip capacitor | 5.1 pF | Murata: Hi-Q SMD 0805 |
| C19, C28 | multilayer ceramic chip capacitor | 6.2 pF | Murata: Hi-Q SMD 0805 |
| C20 | multilayer ceramic chip capacitor | 1 pF | Murata: Hi-Q SMD 0805 |
| C21 | multilayer ceramic chip capacitor | 10 pF | Murata: Hi-Q SMD 0805 |
| C26, C27 | electrolytic capacitor | 1000 μF , 100 V | |
| R1, R3 | resistor | 5.1 Ω | SMD 0805 |
| R2 | resistor | 50 Ω | SMD 2512 |
| X1 | hybrid coupler | 2 dB, 90° | X3C7F1-02S |
| X2 | attenuator | 1 dB; 10 W | D10AA1Z4 |

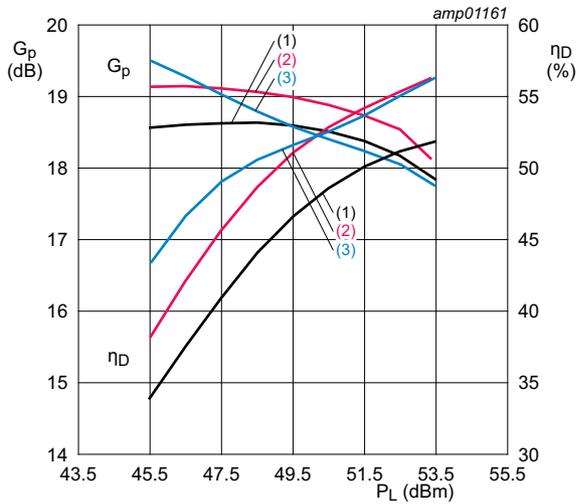
7.4 Graphical data

7.4.1 Pulsed CW



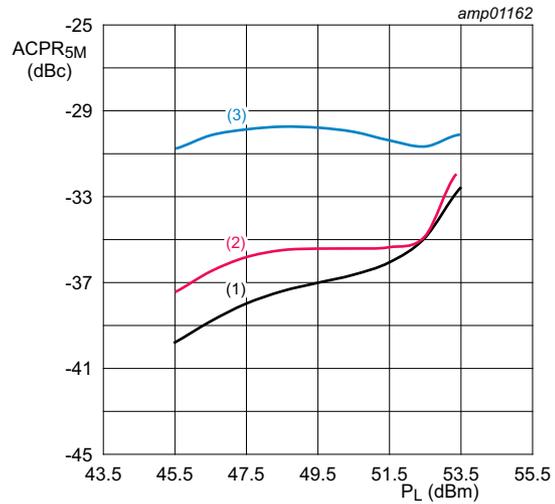
7.4.2 1-Carrier W-CDMA

Test signal: 1-carrier W-CDMA; PAR = 7.2 dB per carrier at 0.01 % probability on CCDF; 3GPP test model 1; 1 to 64 DPCH.



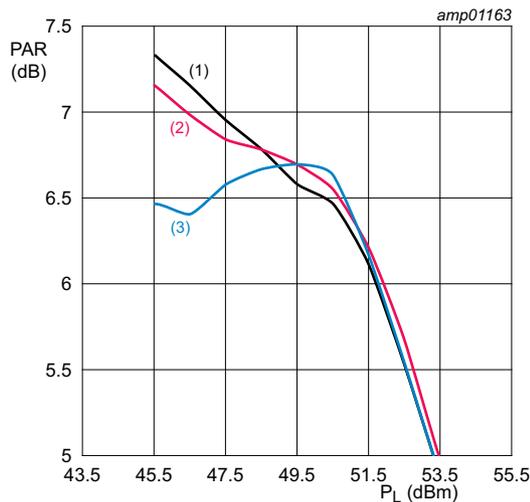
$V_{DS} = 48\text{ V}; I_{Dq} = 550\text{ mA}; V_{GS(amp)peak} = 0.5\text{ V}.$
 (1) $f = 760.5\text{ MHz}$
 (2) $f = 780\text{ MHz}$
 (3) $f = 800.5\text{ MHz}$

Fig 4. Power gain and drain efficiency as function of output power; typical values



$V_{DS} = 48\text{ V}; I_{Dq} = 550\text{ mA}; V_{GS(amp)peak} = 0.5\text{ V}.$
 (1) $f = 760.5\text{ MHz}$
 (2) $f = 780\text{ MHz}$
 (3) $f = 800.5\text{ MHz}$

Fig 5. Adjacent channel power ratio (5 MHz) as a function of output power; typical values



$V_{DS} = 48\text{ V}; I_{Dq} = 550\text{ mA}; V_{GS(amp)peak} = 0.5\text{ V}.$
 (1) $f = 760.5\text{ MHz}$
 (2) $f = 780\text{ MHz}$
 (3) $f = 800.5\text{ MHz}$

Fig 6. Peak-to-average power ratio as a function of output power; typical values

8. Package outline

Plastic earless flanged cavity package; 4 leads

SOT1250-4

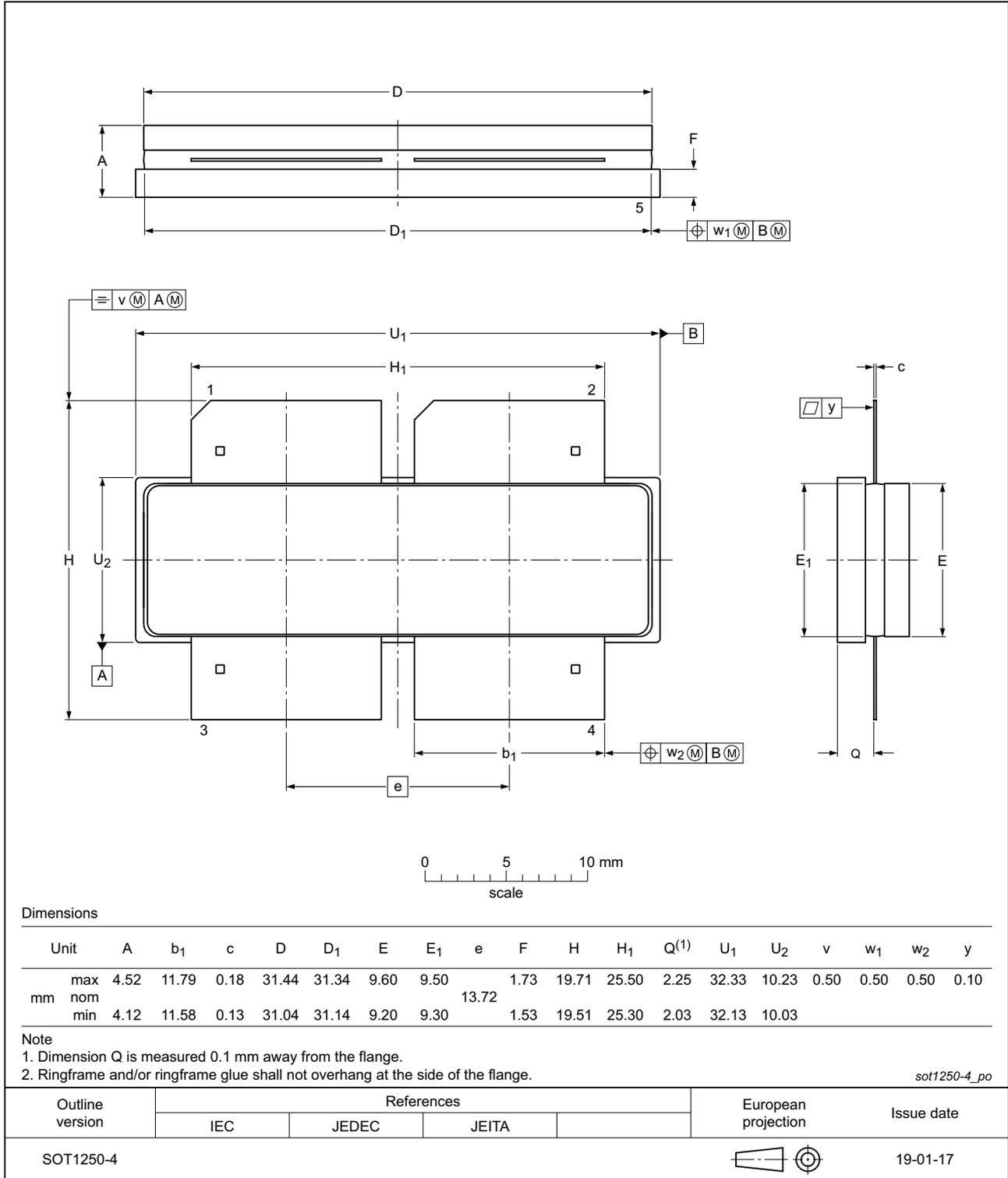


Fig 7. Package outline SOT1250-4

9. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the *ANSI/ESD S20.20*, *IEC/ST 61340-5*, *JESD625-A* or equivalent standards.

Table 15. ESD sensitivity

| ESD model | Class |
|--|------------------------|
| Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002 | C3 [1] |
| Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001 | 2 [2] |

[1] CDM classification C3 is granted to any part that passes after exposure to an ESD pulse of ≥ 1000 V.

[2] HBM classification 2 is granted to any part that passes after exposure to an ESD pulse of 2000 V.

10. Abbreviations

Table 16. Abbreviations

| Acronym | Description |
|---------|--|
| 3GPP | 3rd Generation Partnership Project |
| CCDF | Complementary Cumulative Distribution Function |
| CW | Continuous Wave |
| DPCH | Dedicated Physical CHannel |
| ESD | ElectroStatic Discharge |
| LDMOS | Laterally Diffused Metal-Oxide Semiconductor |
| MTF | Median Time to Failure |
| OBO | Output Back Off |
| PAR | Peak-to-Average Ratio |
| RoHS | Restriction of Hazardous Substances |
| SMD | Surface Mounted Device |
| VSWR | Voltage Standing Wave Ratio |
| W-CDMA | Wideband Code Division Multiple Access |

11. Revision history

Table 17. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|--------------------|--------------|--------------------|---------------|------------|
| BLC9H10XS-606A v.1 | 20200324 | Product data sheet | - | - |

12. Legal information

12.1 Data sheet status

| Document status ^{[1][2]} | Product status ^[3] | Definition |
|-----------------------------------|-------------------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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For sales office addresses, please visit: <http://www.ampleon.com/sales>

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